



Fig.1.

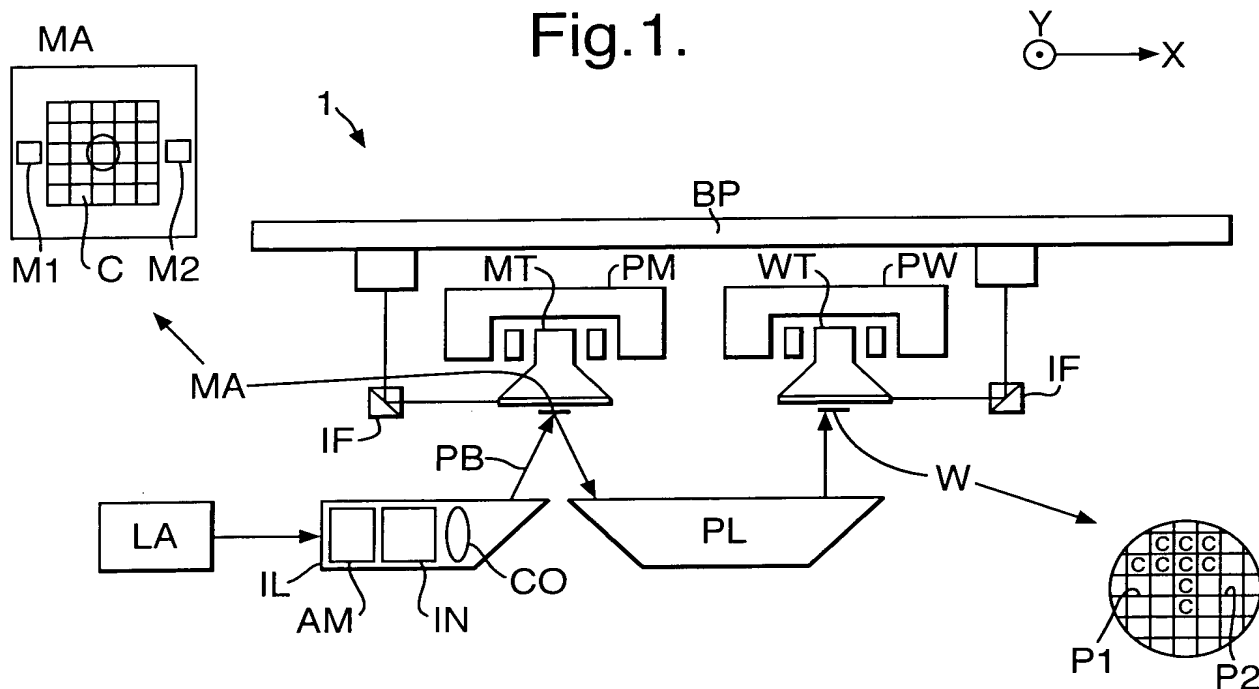


Fig.2.

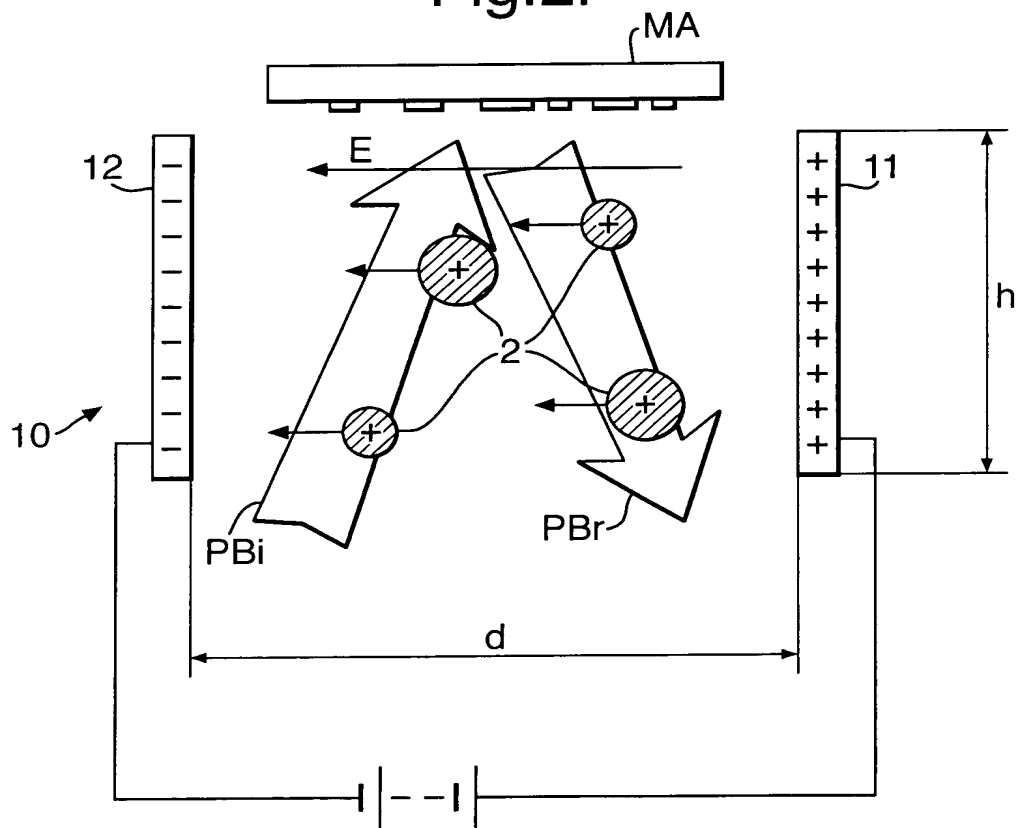


Fig.3.

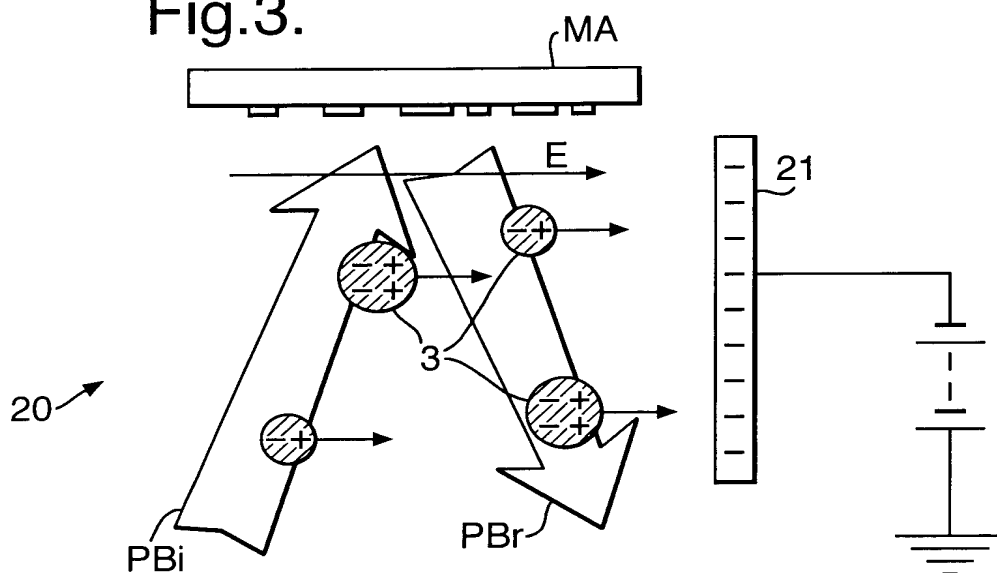


Fig.4.

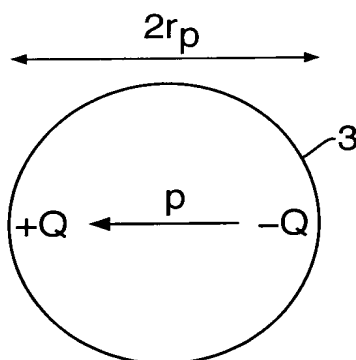


Fig.5.

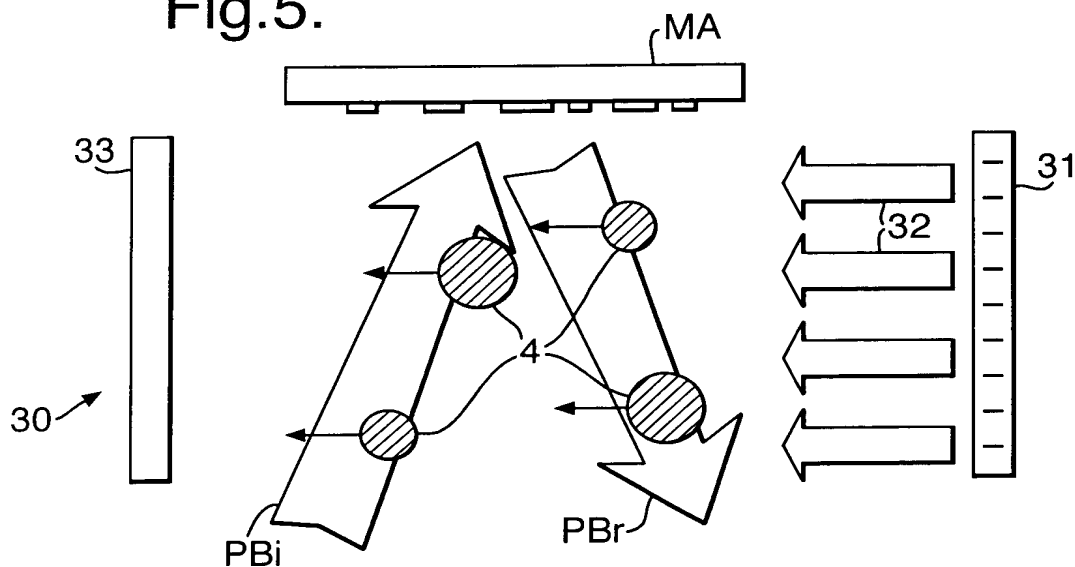




Fig.6.

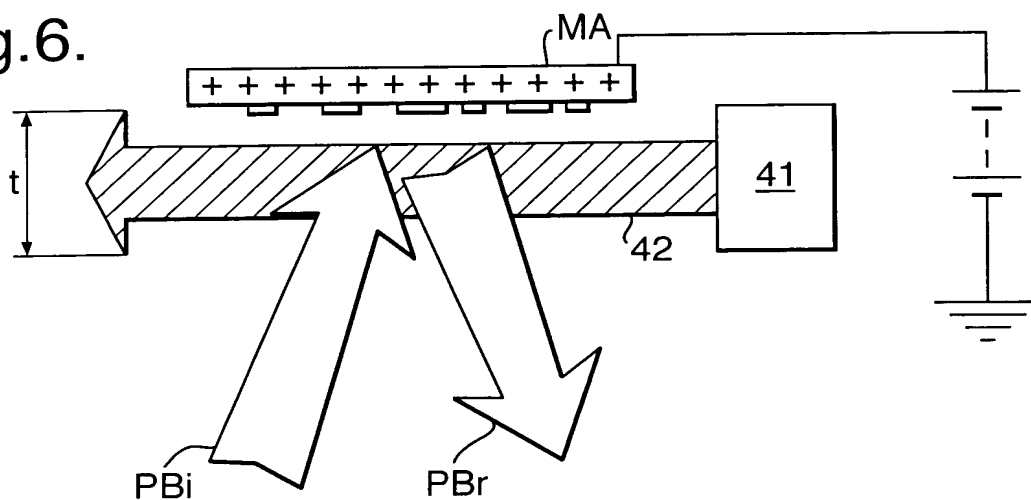


Fig.7.

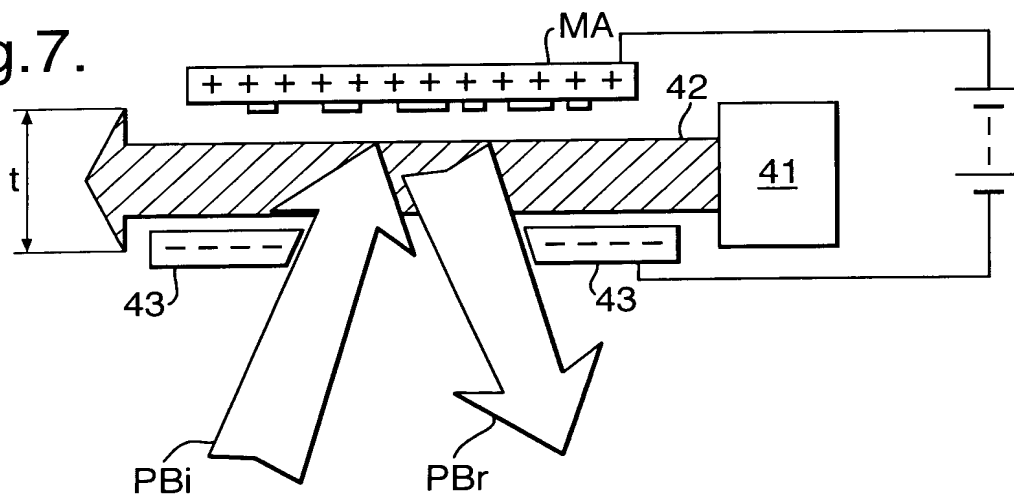


Fig.8.

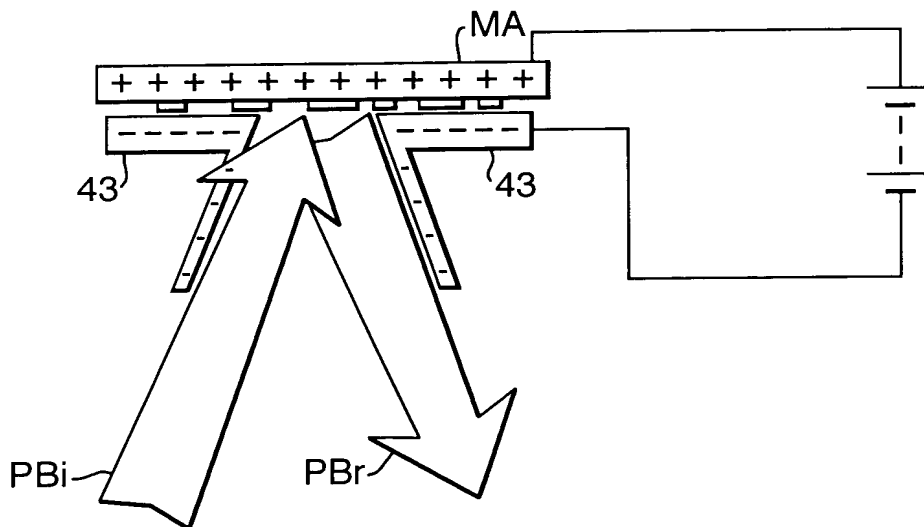




Fig.9.

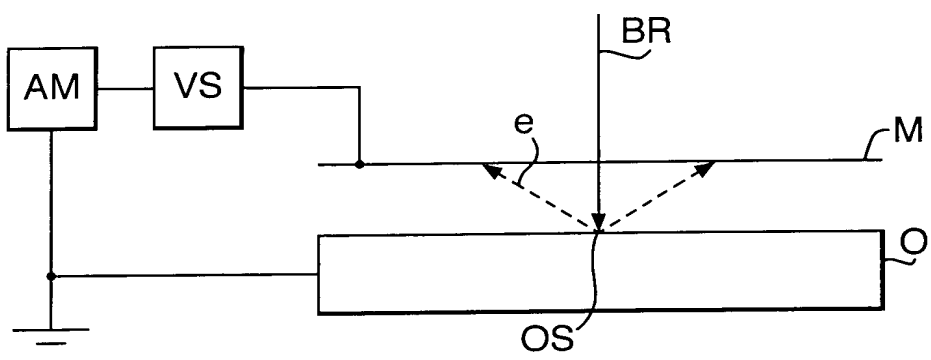
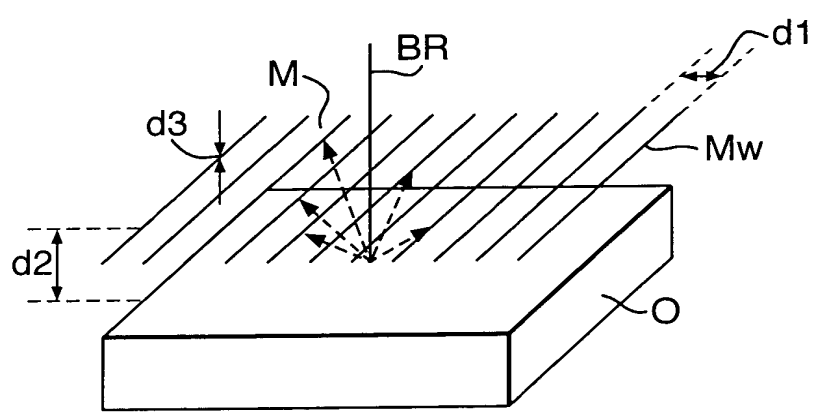


Fig.10.



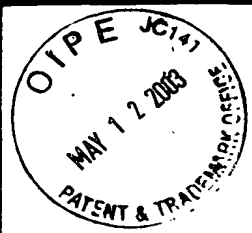


Fig.11.

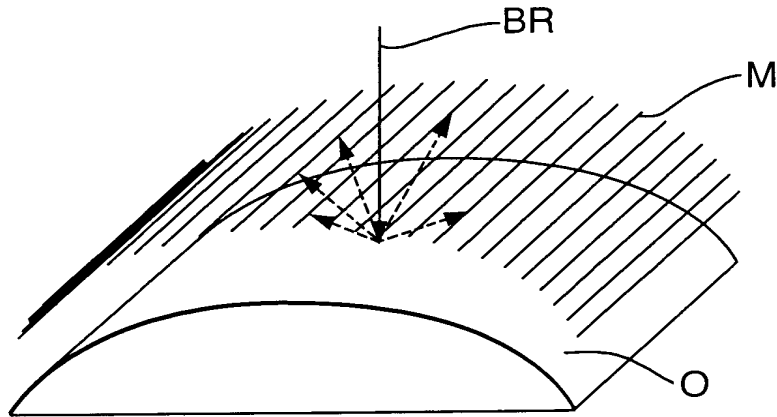
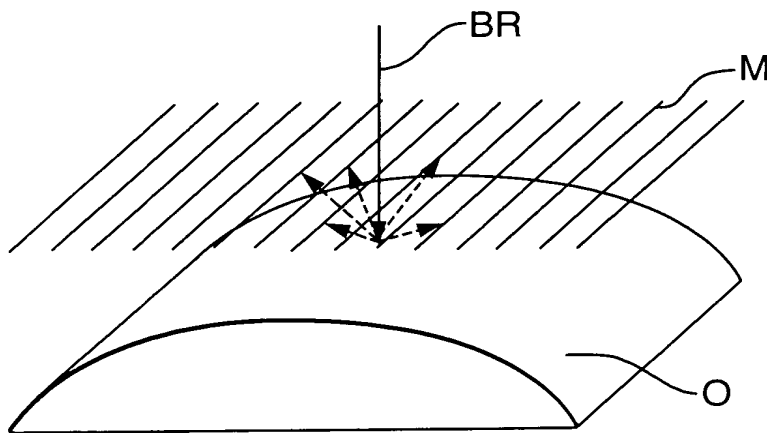


Fig.12.



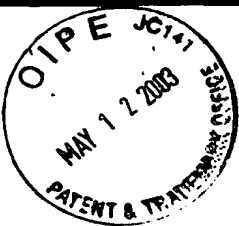


Fig.13.

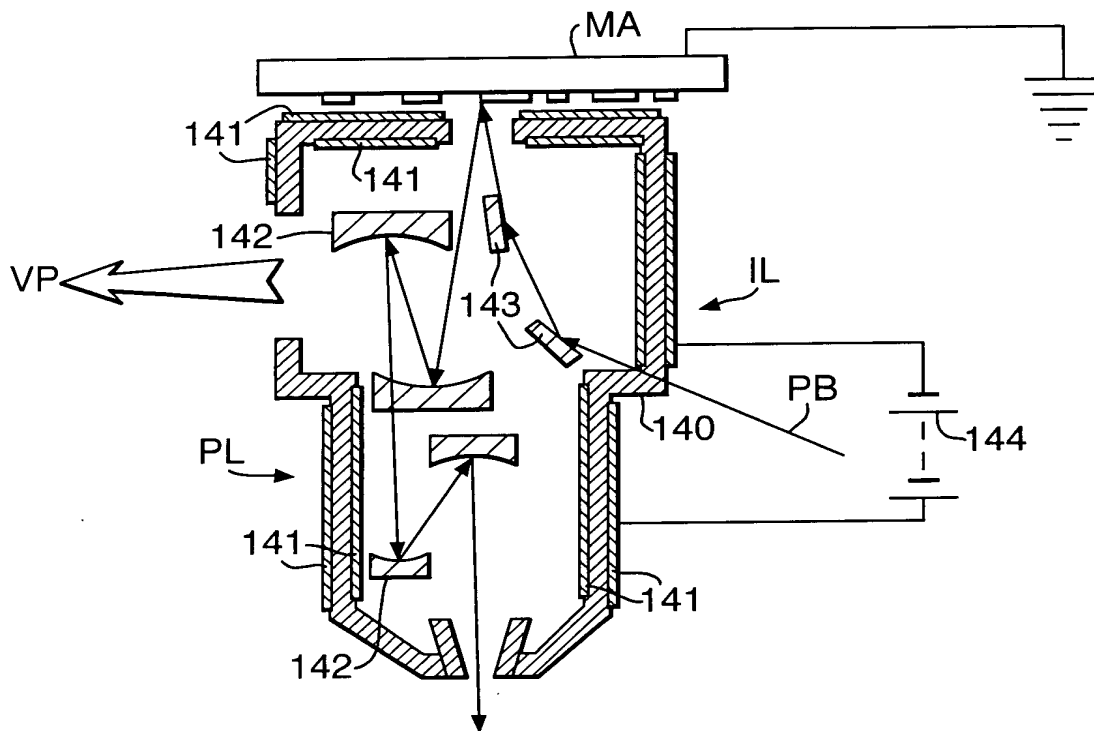


Fig.14.

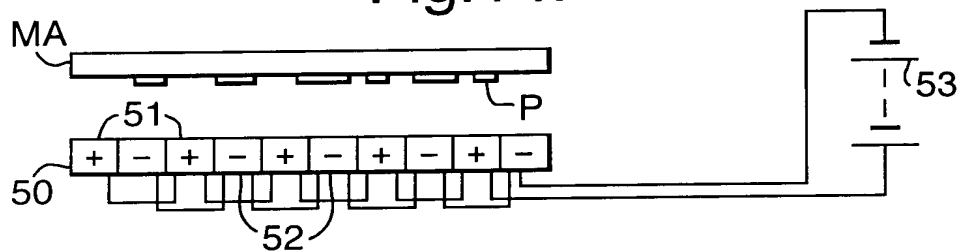
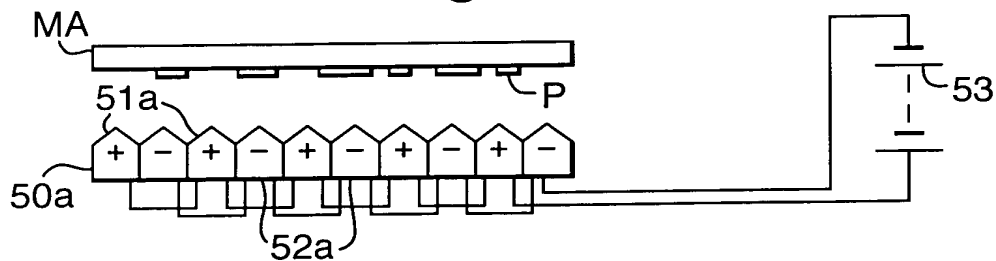


Fig.15.



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Fig. 15a

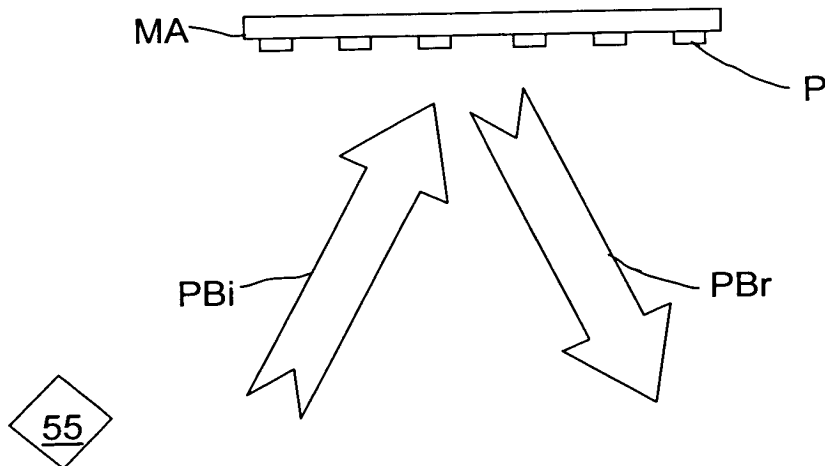
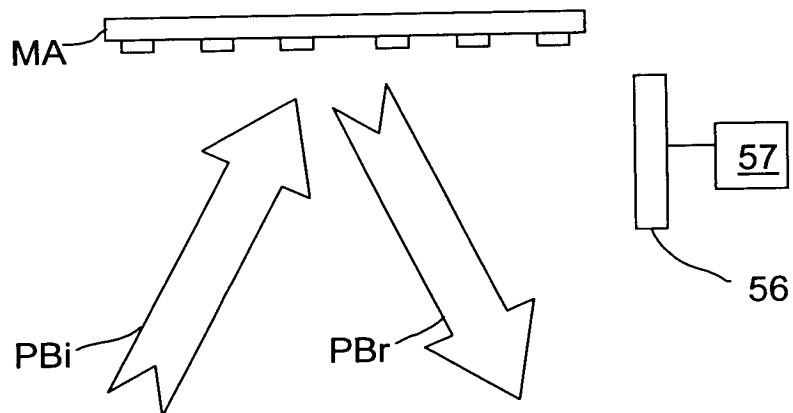
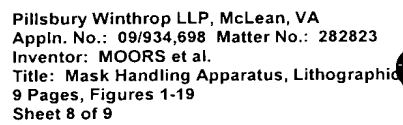


Fig. 15b





A cross-sectional view of a substrate 60. A series of protrusions 61 are formed on the top surface of the substrate. A gap or recessed portion 62 is located between the protrusions.

A cross-sectional view of a semiconductor device. A substrate 71 contains a trench 72. A gate structure 73 is formed on the side wall of the trench. A gate oxide layer 74 is formed on the bottom of the trench. A gate electrode 75 is formed on the gate oxide layer. A gate voltage source 76 is connected to the gate electrode. The gate voltage source is represented by a battery symbol with a dashed line and a solid line, and is labeled with a voltage V .

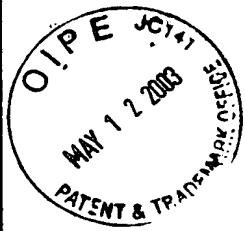


Fig.19.

